

HZM6.2ZFA

Silicon Epitaxial Planar Zener Diode for Surge Absorb

HITACHI

ADE-208-593(Z)

Rev 0

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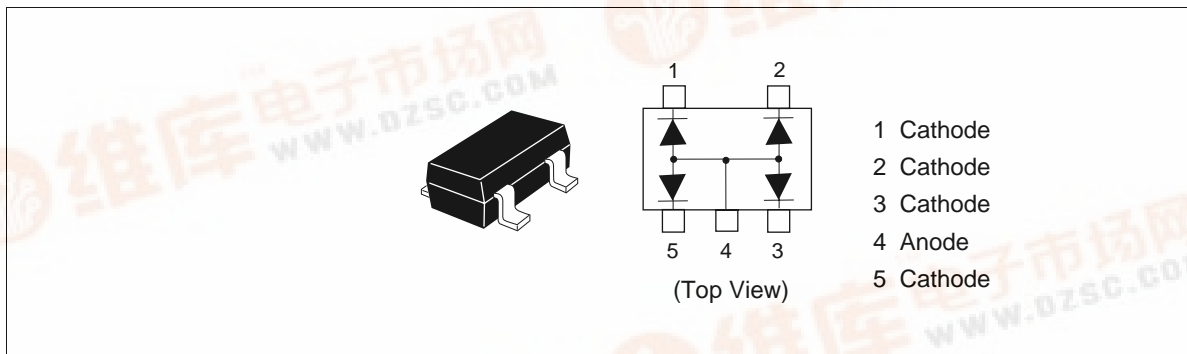
Features

- HZM6.2ZFA has four devices, and can absorb external + and -surge.
- Low capacitance ($C=8.5\text{pF}$ max) and can protect ESD of signal line.
- MPAK-5 Package is suitable for high density surface mounting and high speed assembly.

Ordering Information

Type No.	Laser Mark	Package Code
HZM6.2ZFA	62Z	MPAK-5

Outline



HZM6.2ZFA

Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Value	Unit
Power dissipation	Pd ^{*1}	200	mW
Junction temperature	Tj	150	°C
Storage temperature	Tstg	-55 to +150	°C

Note 1. Four device total, See Fig.2.

Electrical Characteristics (Ta = 25°C) ^{*1}

Item	Symbol	Min	Typ	Max	Unit	Test Condition
Zener voltage	V _Z	5.90	—	6.50	V	I _Z = 5 mA, 40ms pulse
Reverse current	I _R	—	—	3	μA	V _R = 5.5V
Capacitance	C	—	8.0	8.5	pF	V _R = 0V, f = 1 MHz
Dynamic resistance	r _d	—	—	60	Ω	I _Z = 5 mA
ESD-Capability ^{*2}	—	13	—	—	kV	C = 150pF, R = 330 Ω, Both forward and reverse direction 10 pulse

Notes 1. Per one device.

2. Failure criterion ; IR > 3 μA at VR = 5.5V.

Main Characteristic

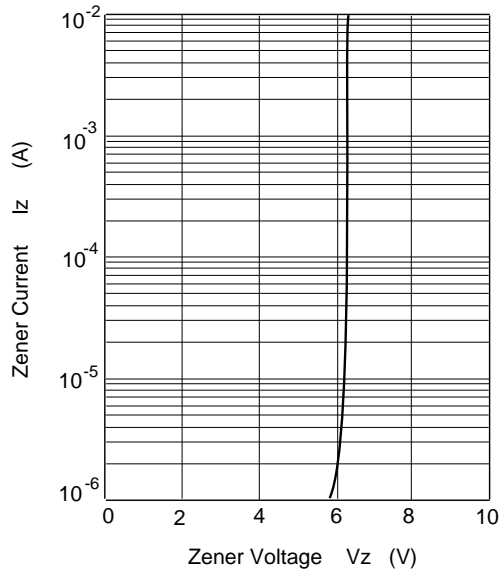


Fig.1 Zener current Vs. Zener voltage

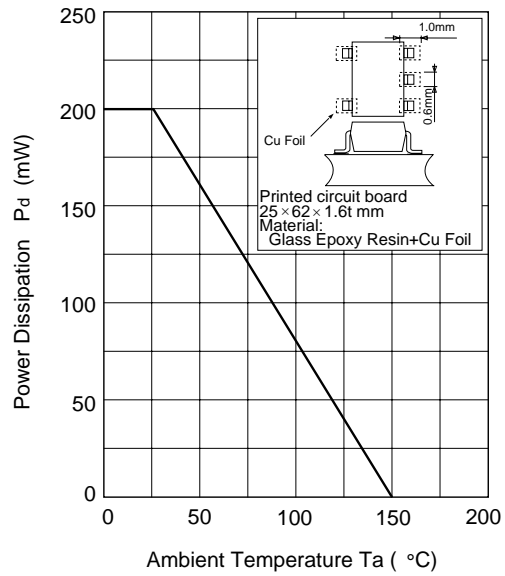


Fig.2 Power Dissipation Vs. Ambient Temperature

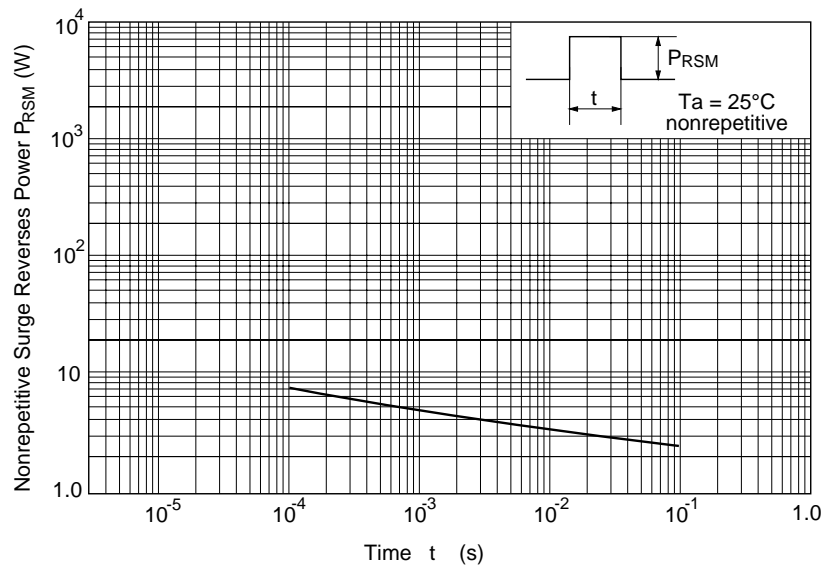


Fig.3 Surge Reverse Power Ratings

HZM6.2ZFA

Main Characteristic

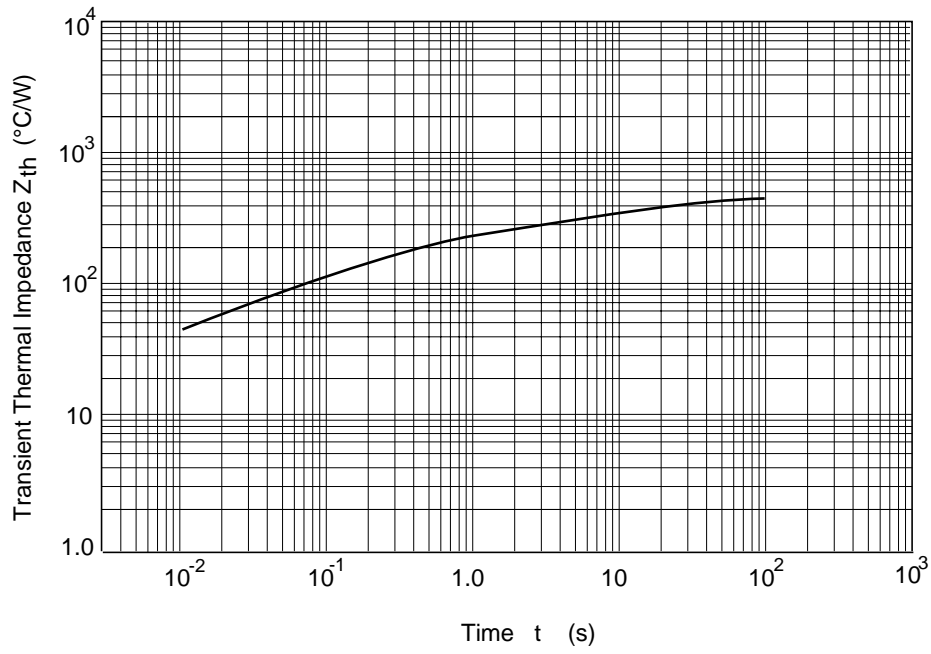
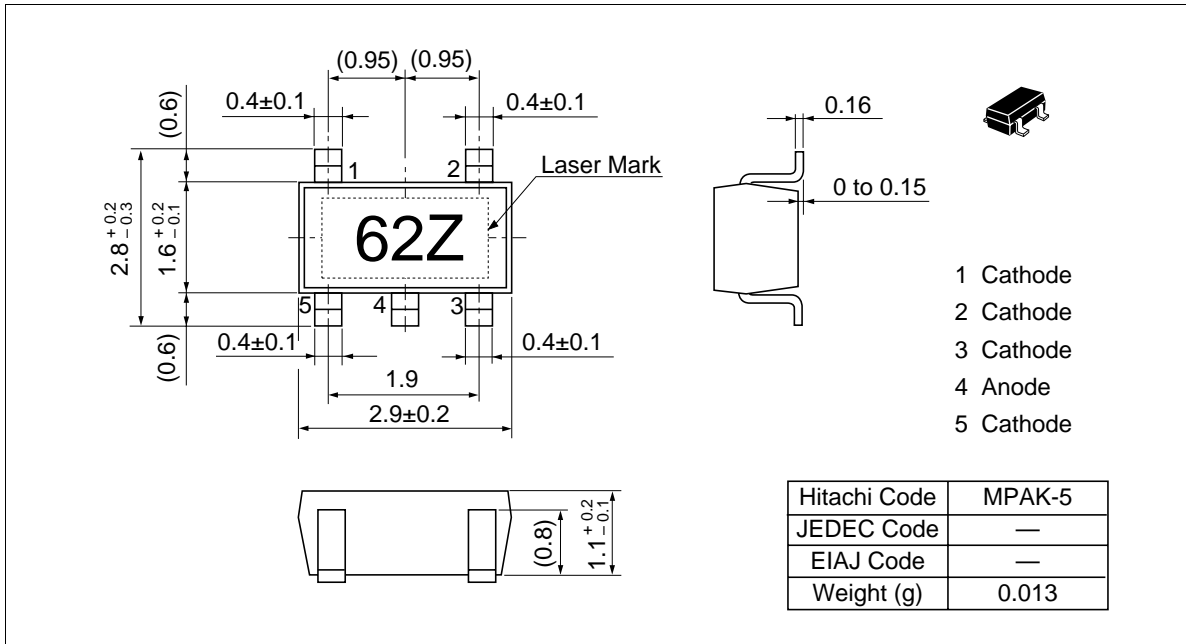


Fig.4 Transient Thermal Impedance

Package Dimensions

Unit : mm



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